

InGaAs / InP PIN Chip ---TK 920M3B

1. Scope

- The specification applies to photo-diode chips for PIN-TIA.
- Type : TK920M3B.

2. Structure

- InGaAs / InP PIN Chip.
- P Electrode (anode) : Gold.
- N Electrode (cathode) : Gold.

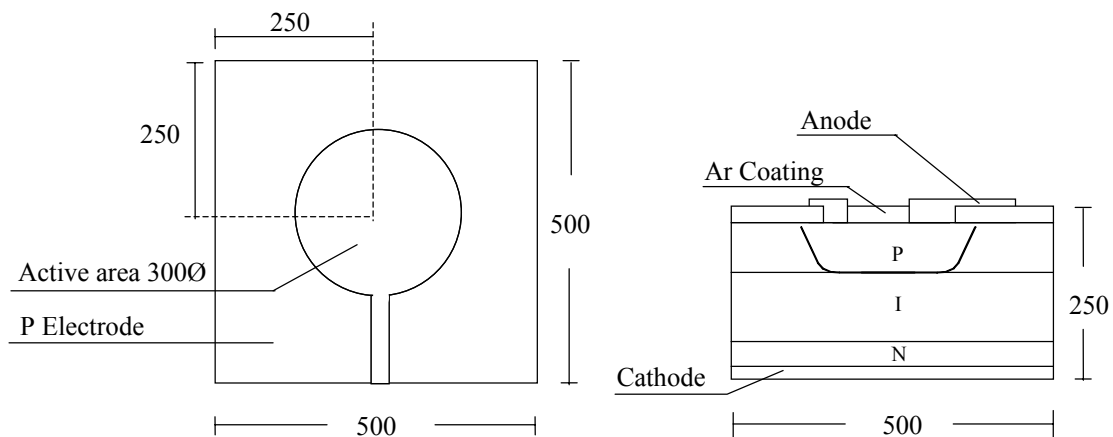
3. Size

- Chip size : $500 \times 500 \mu\text{m}$
- Thickness : $250 \mu\text{m}$
- Active area : $300 \mu\text{m}$ (diameter)
- Pattern drawing : per fig. 1

4. Electro-Optical Characteristics

($T_a = +25 \text{ }^\circ\text{C}$)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Responsivity	R	$V_r=5\text{V}, \lambda=1300 \text{ nm}$	0.9	1		A/W
Dark Current	I_d	$V_r=5\text{V}$		1	5	nA



Unit : μm

fig. 1

2002 Sep.



TYNTEK Head Office
 TYNTEK Chunan Branch
<http://www.tyntek.com.tw>

Tel : 886-3-5781616

Tel : 886-37-582997

E-mail : service@serv.tyntek.com.tw

Fax : 886-3-5780545

Fax : 886-37-582908